



STP7NC70Z - STP7NC70ZFP STB7NC70Z - STB7NC70Z-1

N-CHANNEL 700V - 1.1Ω - 6A TO-220/FP/D²PAK/I²PAK

Zener-Protected PowerMESH™III MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP7NC70Z/FP	700V	< 1.38Ω	6 A
STB7NC70Z/-1	700V	< 1.38Ω	6 A

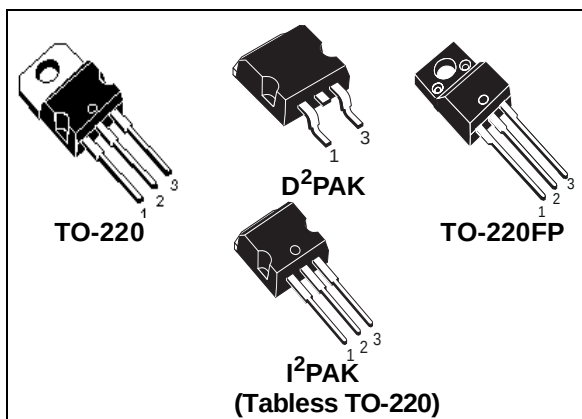
- TYPICAL R_{DS(on)} = 1.1Ω
- EXTREMELY HIGH dv/dt AND CAPABILITY GATE TO - SOURCE ZENER DIODES
- 100% AVALANCHE TESTED
- VERY LOW GATE INPUT RESISTANCE
- GATE CHARGE MINIMIZED

DESCRIPTION

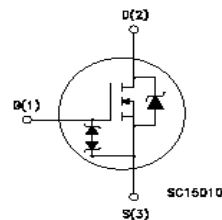
The third generation of MESH OVERLAY™ Power MOSFETs for very high voltage exhibits unsurpassed on-resistance per unit area while integrating back-to-back Zener diodes between gate and source. Such arrangement gives extra ESD capability with higher ruggedness performance as requested by a large variety of single-switch applications.

APPLICATIONS

- SINGLE-ENDED SMPS IN MONITORS, COMPUTER AND INDUSTRIAL APPLICATION
- WELDING EQUIPMENT



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP(B)7NC70Z(-1)	STP7NC70ZFP	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	700		V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	700		V
V _{GS}	Gate- source Voltage	± 25		V
I _D	Drain Current (continuous) at T _C = 25°C	6	6(*)	A
I _D	Drain Current (continuous) at T _C = 100°C	3.7	3.7(*)	A
I _{DM} (1)	Drain Current (pulsed)	24	24	A
P _{TOT}	Total Dissipation at T _C = 25°C	125	40	W
	Derating Factor	1	0.32	W/°C
I _{GS}	Gate-source Current	±50		mA
V _{ESD(G-S)}	Gate source ESD(HBM-C=100pF, R=15KΩ)	3		KV
dv/dt	Peak Diode Recovery voltage slope	3		V/ns
V _{ISO}	Insulation Withstand Voltage (DC)	--	2000	V
T _{stg}	Storage Temperature	-65 to 150		°C
T _j	Max. Operating Junction Temperature	150		°C

(•)Pulse width limited by safe operating area

(1)I_{SD} ≤ 6A, di/dt ≤ 100A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}

(2)Limited only by maximum temperature allowed

THERMAL DATA

		TO-220 / D ² PAK / I ² PAK	TO-220FP	
R _{thj-case}	Thermal Resistance Junction-case Max	1	3.13	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient Max	62.5		°C/W
T _I	Maximum Lead Temperature For Soldering Purpose	300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	6	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	238	mJ

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)
OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	700			V
ΔBV _{DSS} /ΔT _j	Breakdown Voltage Temp. Coefficient	I _D = 1 mA, V _{GS} = 0		0.8		V/°C
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 50	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ±20V			±10	μA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	3	4	5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 3.5 A		1.1	1.38	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} , I _D = 3.5A		7		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		1840		pF
C _{oss}	Output Capacitance			140		pF
C _{rss}	Reverse Transfer Capacitance			18		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 350\text{ V}$, $I_D = 3.5\text{ A}$		24		ns
t_r	Rise Time	$R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		8		ns
Q_g	Total Gate Charge	$V_{DD} = 560\text{ V}$, $I_D = 7\text{ A}$, $V_{GS} = 10\text{ V}$		47	66	nC
Q_{gs}	Gate-Source Charge			11		nC
Q_{gd}	Gate-Drain Charge			19		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(voff)}$	Off-voltage Rise Time	$V_{DD} = 560\text{ V}$, $I_D = 7\text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$		11		ns
t_f	Fall Time	(see test circuit, Figure 5)		10		ns
t_c	Cross-over Time			19		ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				6	A
$I_{SDM}(2)$	Source-drain Current (pulsed)				24	A
$V_{SD}(1)$	Forward On Voltage	$I_{SD} = 6\text{ A}$, $V_{GS} = 0$			1.6	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 50\text{ V}$, $T_J = 150^\circ\text{C}$		575		ns
Q_{rr}	Reverse Recovery Charge	(see test circuit, Figure 5)		5.8		μC
I_{RRM}	Reverse Recovery Current			20		A

GATE-SOURCE ZENER DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-Source Breakdown Voltage	$I_{GS} = \pm 1\text{ mA}$ (Open Drain)	25			V
αT	Voltage Thermal Coefficient	$T = 25^\circ\text{C}$ Note(3)		1.3		$10^{-4}/^\circ\text{C}$
R_z	Dynamic Resistance	$I_D = 50\text{ mA}$, $V_{GS} = 0$		90		Ω

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

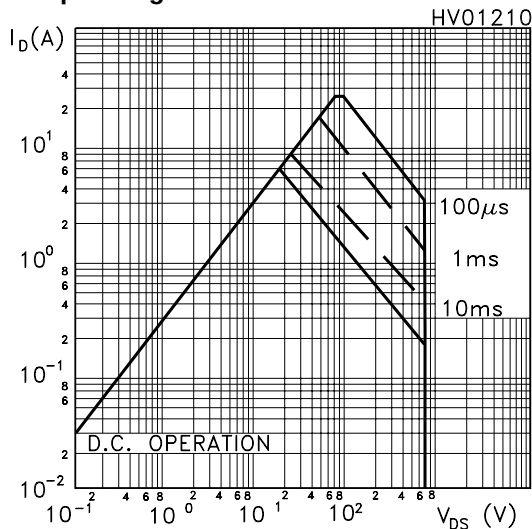
2. Pulse width limited by safe operating area.

3. $\Delta V_{BV} = \alpha T$ ($25^\circ - T$) $BV_{GSO}(25^\circ)$

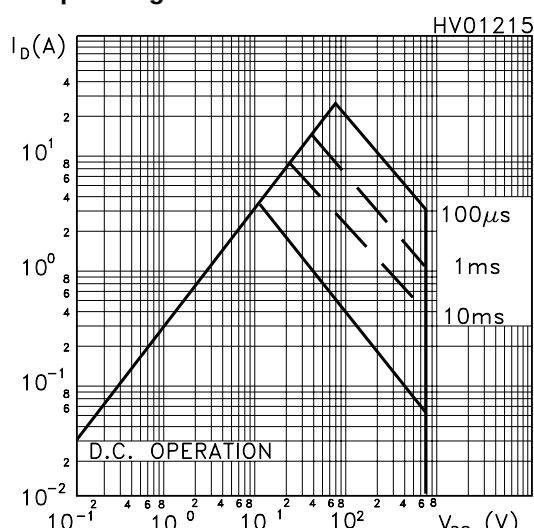
PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

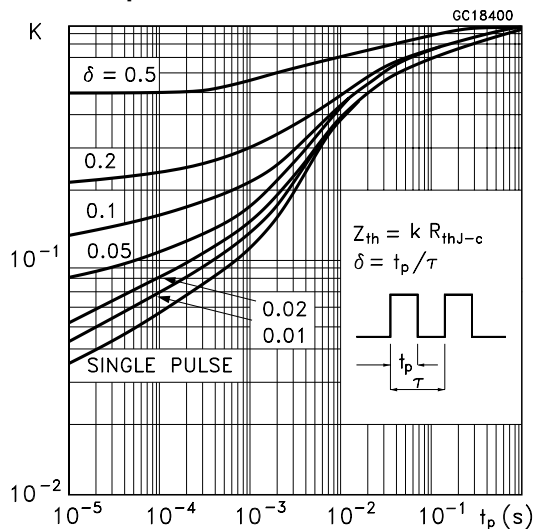
Safe Operating Area For TO-220/D2PAK/I2PAK



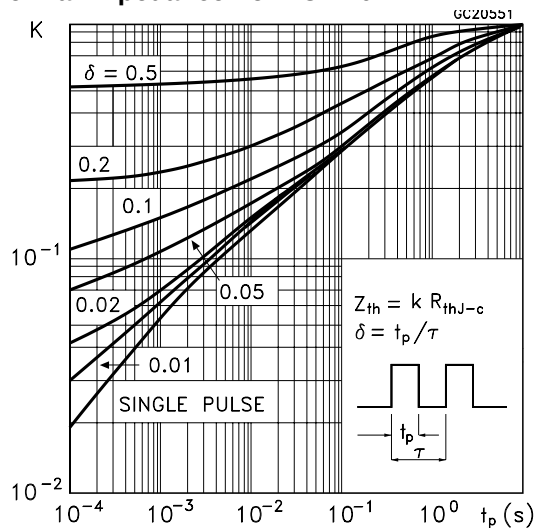
Safe Operating Area For TO-220FP



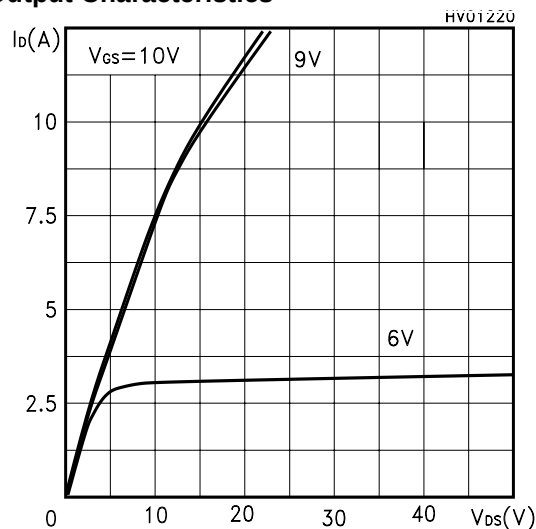
Thermal Impedance For TO-220/D2PAK/I2PAK



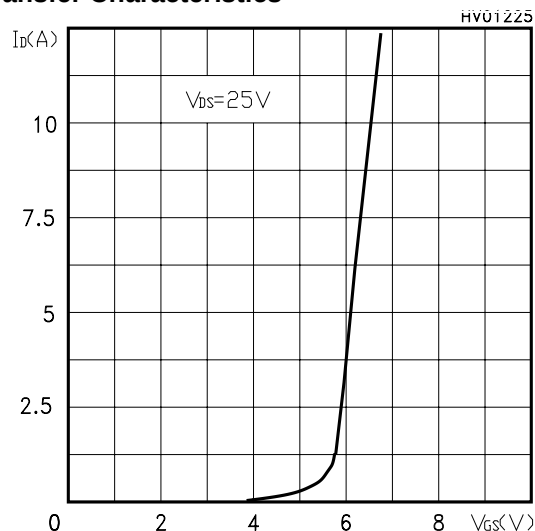
Thermal Impedance For TO-220FP



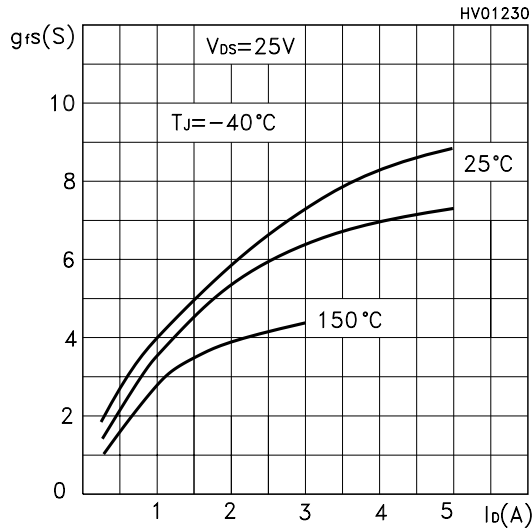
Output Characteristics



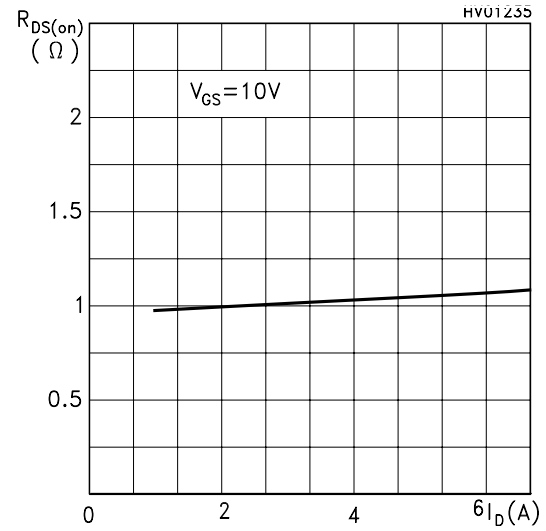
Transfer Characteristics



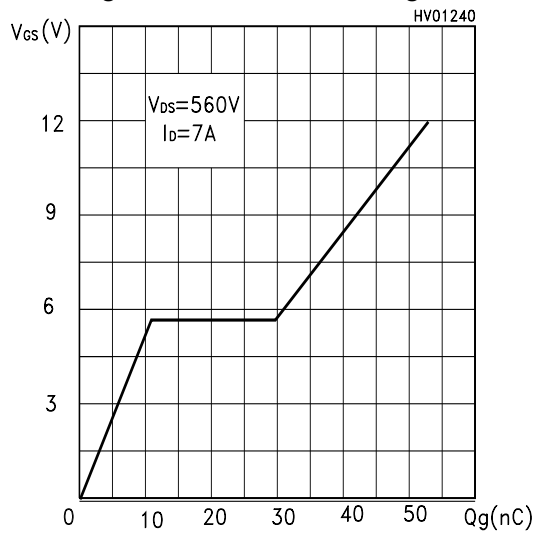
Transconductance



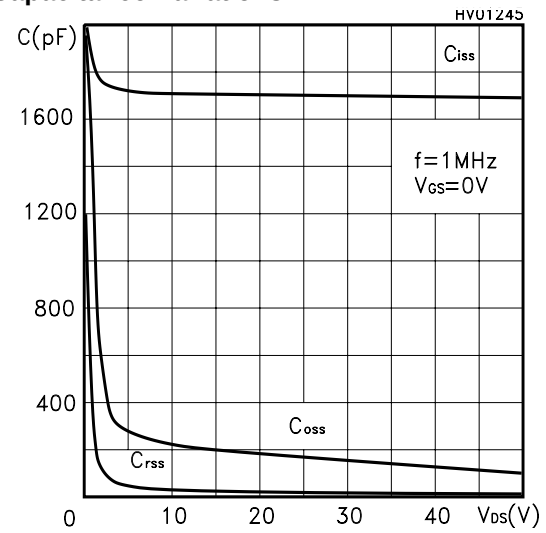
Static Drain-source On Resistance



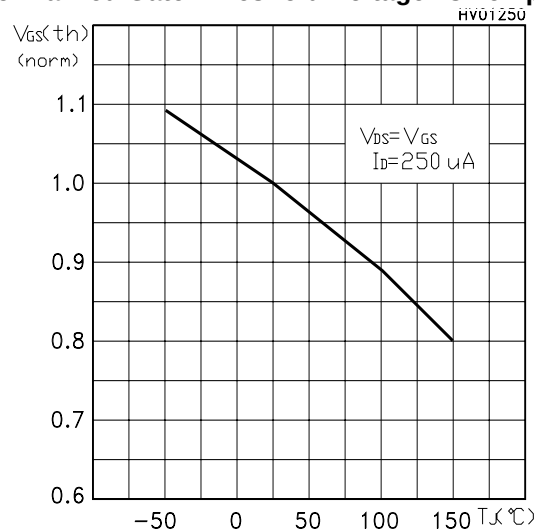
Gate Charge vs Gate-source Voltage



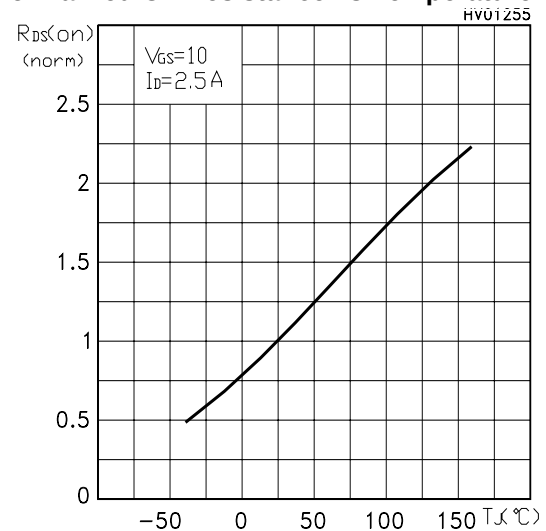
Capacitance Variations



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

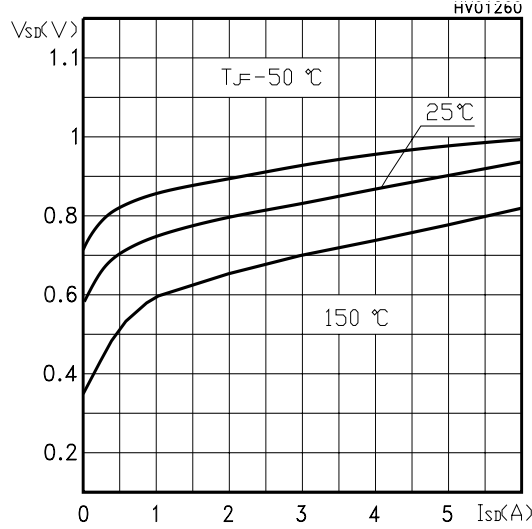


Fig. 1: Unclamped Inductive Load Test Circuit

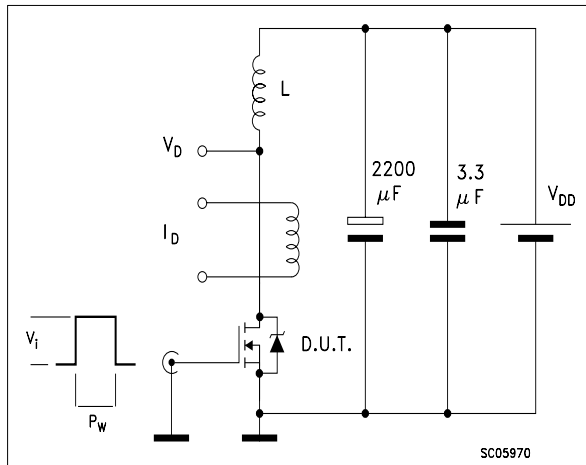


Fig. 2: Unclamped Inductive Waveform

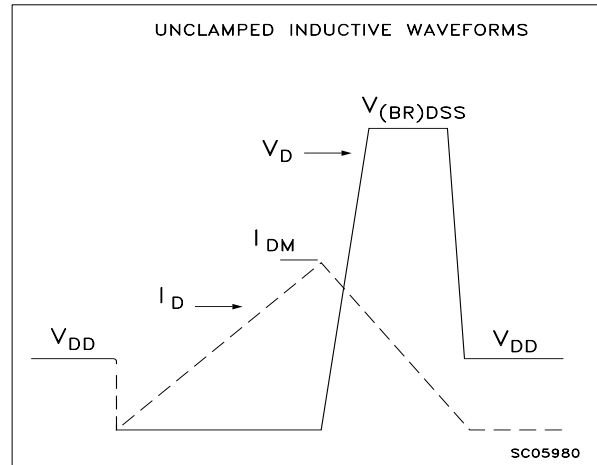


Fig. 3: Switching Times Test Circuits For Resistive Load

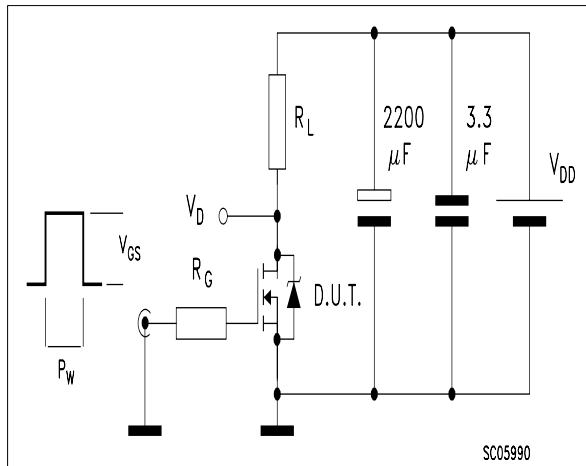


Fig. 4: Gate Charge test Circuit

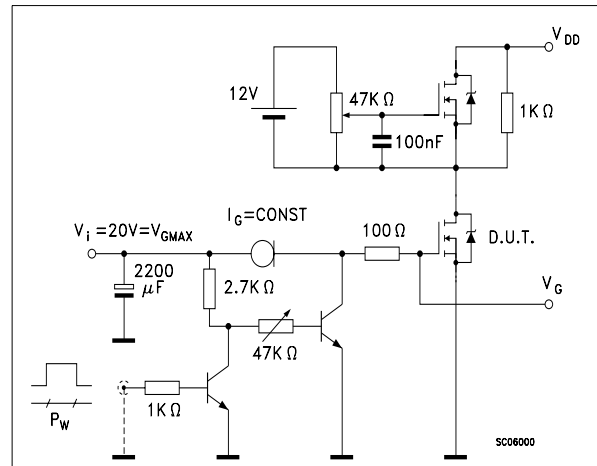
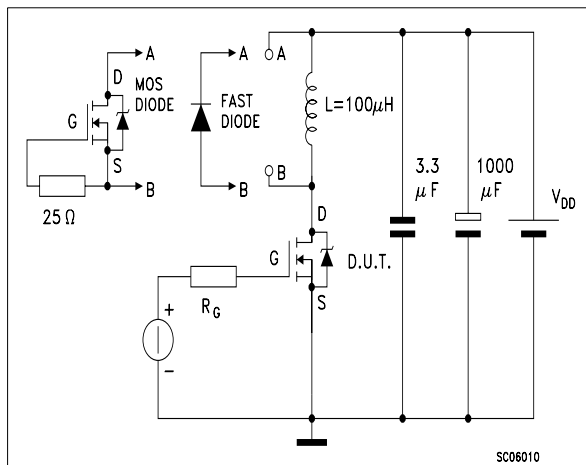
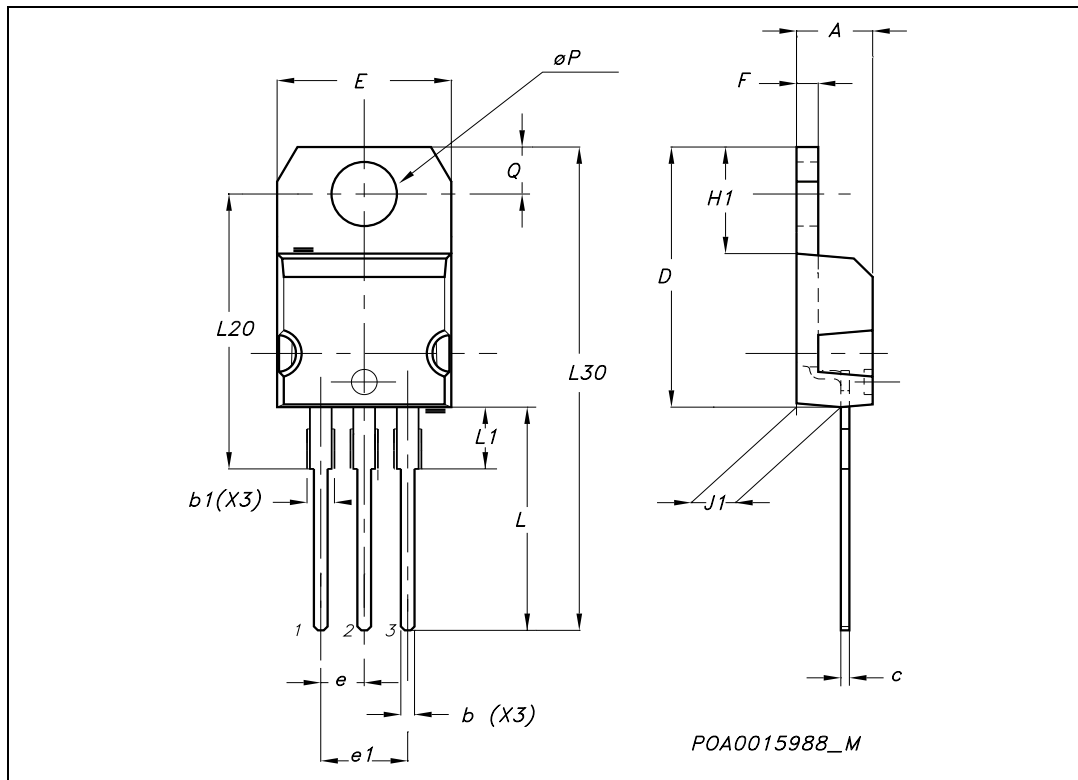


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



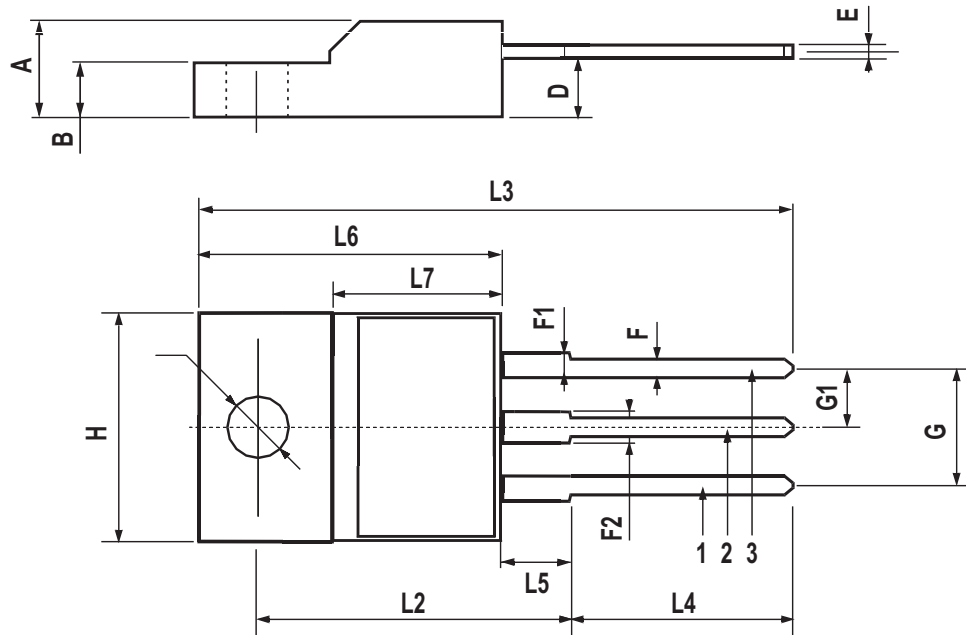
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



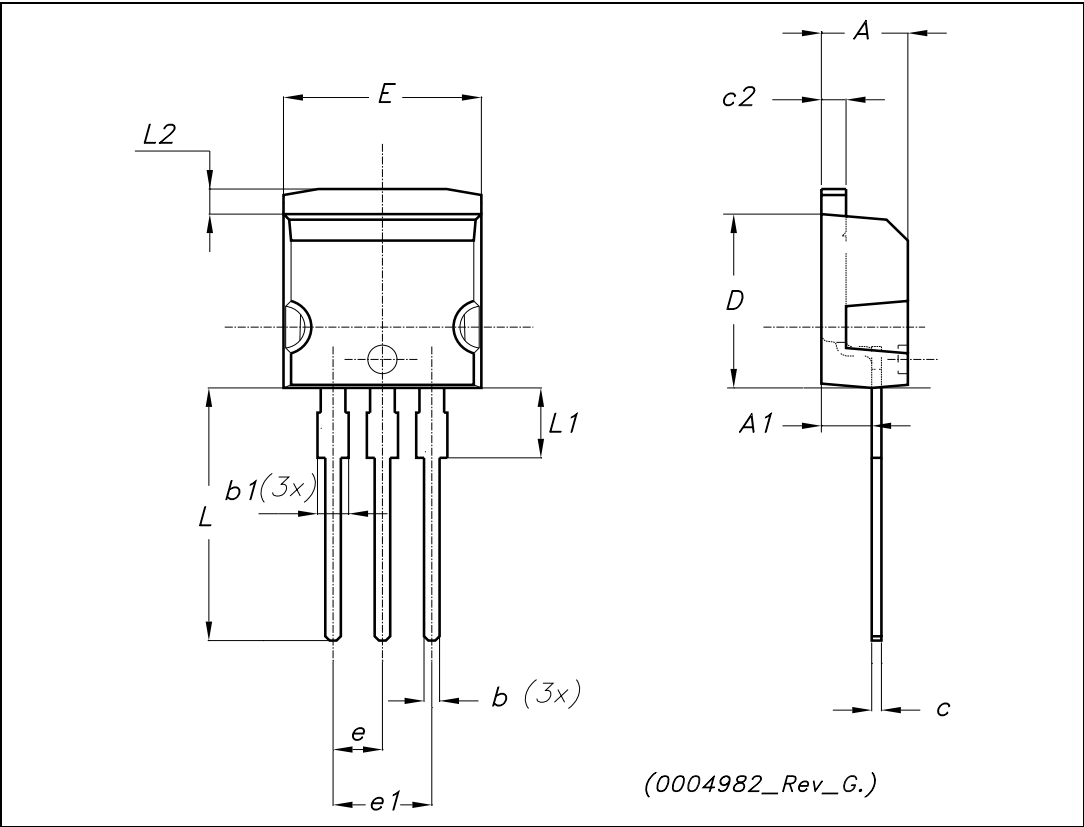
TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.5	0.045		0.067
F2	1.15		1.5	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



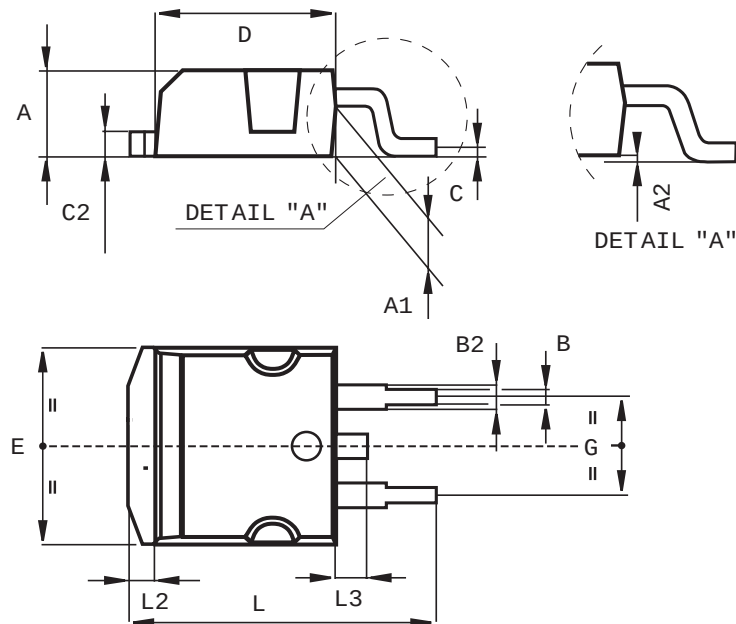
TO-262 (I²PAK) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



TO-263 (D²PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.21		1.36	0.047		0.053
D	8.95		9.35	0.352		0.368
E	10		10.4	0.393		0.409
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068



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